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(21) International Application Number: PCT/US99/05968 (22) International Filing Date: 18 March 1999 (18.03.99) (30) Priority Data: 09/040,630 18 March 1998 (18.03.98) US (71) Applicant: CABOT CORPORATION [US/US]; 75 State Street, Boston, MA 02109-1806 (US). (72) Inventors: KAUFMAN, Vlasta, Brusic; 721 Easton Avenue, Geneva, IL 60134 (US). KISTLER, Rodney, C.; 912 Harbor Town Court, Geneva, IL 60134 (US). WANG, Shumin; 1006 Dakota Circle, Naperville, IL 60563 (US). (74) Agent: LANDO, Michelle, B.; Cabot Corporation, 157 Concord Road, P.O. Box 7001, Billerica, MA 01821-7001 (US).		(81) Designated States: AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, CA, CH, CN, CZ, DE, DK, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MD, MG, MK, MN, MW, MX, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, UA, UG, UZ, VN, YU, ZW, ARIPO patent (GH, GM, KE, LS, MW, SD, SL, SZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG). Published <i>With international search report.</i> <i>Before the expiration of the time limit for amending the claims and to be republished in the event of the receipt of amendments.</i>
(54) Title: CHEMICAL MECHANICAL POLISHING SLURRY USEFUL FOR COPPER SUBSTRATES (57) Abstract A chemical mechanical polishing slurry comprising an oxidizing agent, a complexing agent, an abrasive, and an optional surfactant, as well as a method for using the chemical mechanical polishing slurry to remove copper alloy, titanium, titanium nitride, tantalum and tantalum nitride containing layers from a substrate. The slurry does not include a separate film-forming agent.		